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SEAT No			No. of printed pages:	03
Day: Thu	A.Sc. Physics sday, Date: 19/ Subject: PHY	I st Semester E. 04/2018, Time: 02 SICS, Paper: PS0	xamination 2:00 p.m. to 05:00 p.m. 01EPHY21	
Instructions: Figures to the right	indicate marks.		Total Marks: 70	
Write answer of number.	all questions by	showing your ch	oice against the question	[8
(a) containin (b) having pe (c) being nat	g different chem riodic spacing o ıral rather than	nical elements of atoms	naterial by	
(ii) An infinite po (a) lattice				
(iii) The group v (a) dω/dt			(d) - dt/dω	
$\frac{\text{by}}{(a)-2\pi} < 1$	$\zeta \leq 2\pi$	(b) - 3π ·	$<$ K \leq 3 π	
(v) In a solid the	re are total	shear and n	ormal stresses. (d) 12	
(a) Infinity ·	(b) zero	(c) positive	(d) negative	
	Day: Thur Title: Instructions: Figures to the right Write answer of number. (i) Crystalline m (a) containing (b) having pe (c) being nate (d) all of the: (ii) An infinite pe (a) lattice (iii) The group ve (a) d\omega/dt (iv) The range of by (a) -2\pi < k (c) -\pi/a < k (c) -\pi/a < k (v) In a solid ther (a) 3 (vi) Under hydro (a) Infinity	SARDAR P M.Sc. Physics Day: Thursday, Date: 19/ Subject: PHY Title: Elements of Sol Instructions: Figures to the right indicate marks. Write answer of all questions by number. (i) Crystalline materials differ for (a) containing different chem (b) having periodic spacing of (c) being natural rather than (d) all of the above (ii) An infinite periodic arranger (a) lattice (b) symmetrical different (a) do/dt (b) dt/do (iv) The group velocity is defined (a) do/dt (b) dt/do (iv) The range of the first Brilloughy (a) -2π < K ≤ 2π (c) -π/a < K ≤ π/a (v) In a solid there are total (a) 3 (b) 6 (vi) Under hydrostatic pressure, (a) Infinity (b) zero	SARDAR PATEL UNIV M.Sc. Physics Ist Semester E Day: Thursday, Date: 19/04/2018, Time: 02 Subject: PHYSICS, Paper: PSO Title: Elements of Solid State Physics a Instructions: Figures to the right indicate marks. Write answer of all questions by showing your change of a containing different chemical elements (b) having periodic spacing of atoms (c) being natural rather than manmade (d) all of the above (ii) An infinite periodic arrangement of points in (a) lattice (b) symmetry (c) zon (iii) The group velocity is defined by: (a) dodd (b) dt/do (c) - dodd (iv) The range of the first Brillouin zone of linear by (a) -2π < K ≤ 2π (b) -3π (c) -π/a < K ≤ π/a (d) -2π/a (v) In a solid there are total shear and in (a) 3 (b) 6 (c) 9 (vi) Under hydrostatic pressure, dilation is (a) Infinity (b) zero (c) positive	SARDAR PATEL UNIVERSITY M.Sc. Physics I st Semester Examination Day: Thursday, Date: 19/04/2018, Time: 02:00 p.m. to 05:00 p.m. Subject: PHYSICS, Paper: PS01EPHY21 Title: Elements of Solid State Physics and Error Analysis Instructions: Figures to the right indicate marks. Total Marks: 70 Write answer of all questions by showing your choice against the question number. (i) Crystalline materials differ from amorphous material by

CP. T.O.)

(c) 20

(c) 18

(d) 2000

(d) $1\overline{9}$

frequency = _

(b) 0.5

(viii) In a histogram, maximum class interval should be

(b) 17

(a) 0.05

(a) 16

Q.2 Attempt any Seven of the following: [14] (i) Define: Unit cell and Primitive cell. (ii) What is packing fraction? Calculate the packing fraction for the BCC structure. (iii) Differentiate between Miller indices and Miller Bravais indices with proper example. (iv) Describe the continuum limit of lattice vibration. (v) Explain in brief thermoelectric effect in semiconductor. $\delta = \in_{xx} + \in_{yy} + \in_{zz}$ (vi) What is dilation? Prove that dilation (vii) Describe impurity conductivity in semiconductor in brief. (viii) Draw the experimental set up used to determine elastic constants of solid and write the equations to determine velocity of shear waves. (ix) Explain the least square method to minimize error in measurements. Q.3(a)Differentiate the terms crystalline and amorphous solids. Write down seven [6] crystal system with their lattice parameters. Draw and describe the crystal structures of the diamond and CsCl giving [6] Q.3(b)coordinates of the atoms with proper illustration. Explain in detail the conventional unit cell of hexagonal close packed (HCP) Q.3(b)

structure using necessary diagram.

Q.4(a) Define lattice vibration and obtain the relation to explain the origin of [6] acoustical and optical branch in linear diatomic lattice.

Q.4(b) Obtain the dispersion relation for one dimensional mono-atomic lattice. [6]

Q.4(b) Explain crystal momentum. Find out the equation of energy gain and loss of [6] the scattered neutrons by phonons.

Q.5(a) Obtain an equation for longitudinal wave and the transverse wave propagate [6] along the [100] direction in a crystal.

Q.5(b) What is intrinsic semiconductor? Derive an expression for the carrier [6] concentration in case of intrinsic semiconductor.

Q.5(b) Using necessary diagram, find out the expression for the longitudinal and [6] transverse waves propagate in the cubic crystal in [111] direction.

Q.6(a) (i) A company manufactures 80 resistors and the resistance of these resistors are given below: [3]

Resistance (ohms)	No. of Resistor
93-95	04
96-98	15
99-101	. 33
102-104	21
105-107	07

Determine: (a) arithmetic mean, (b) The median value and (c) modal value.

- (ii) Prove that arithmetic mean is the best estimated true value of the data. [3]
- Q.6(b) (i) What is Gaussian distribution? Determine standard deviation from Gaussian distribution. [3]
 - (ii) In a manufacturing process, 25 components have been selected.

 75 minutes is mean time required to complete a electronic components and standard deviation is 10 minutes.

 [3]

Calculate:

- (a) Population of mean,
- (b) Standard deviation of the mean and
- (c) Size of the sample.

Internal standard error is not to exceed 1 min.

OR

Q.6(b) Explain Chi-square test for goodness of fit and the criteria for goodness of fit. [6]

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